

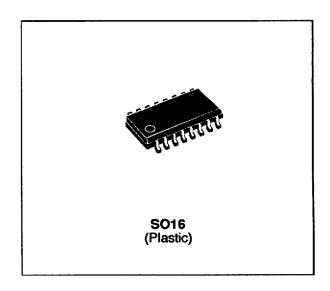
ICC01-400B5

Application Specific Discretes A.S.D.™

IGNITION CONTROL CIRCUIT

FEATURES AND BENEFITS

- MONOLITHIC CIRCUIT FOR CAPACITANCE DISCHARGE SYSTEM CONTROL.
- DEDICATED THYRISTOR STRUCTURE FOR IGNITION OPERATION.
- APPLICATION SPECIFIC DISCRETES (ASDIM).
- SURFACE AREA REDUCTION.
- SO16 PACKAGE.



DESCRIPTION

The ICC01 is a high-performance planar-diffused technology adapted to rugged environment conditions.

It has been developed especially for small engines using a capacitor discharge technique for ignition operation.

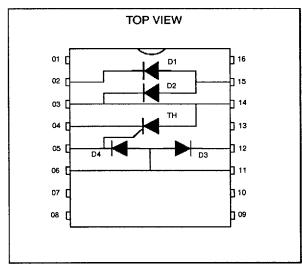
The ICC01 assumes electronics control of the ignition system.

Pin 2 : Motor stop
 Pin 4/6/11 : Ground
 Pin 5 : Sensor

Pin 3/14 : Ignition capacitor
Pin 12/15 : Charging, winding
Pin 1/7/8/9/10/13/16: Not connected

See basic application and functionality page 4.

FUNCTIONAL DIAGRAM



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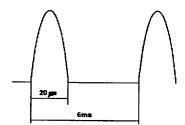
ABSOLUTE MAXIMUM RATINGS: THYRISTOR TH

Symbol	Parameter		Value	Unit
I _{TRM}	Repetitive peak on-state current (Note1)	TI=110°C	100	A
Ітѕм	Non repetitive surge peak on-state current Tj initial = T_j = 25°C	tp = 20 μs	150	А
		tp = 10 ms	5	A
V _{DRM}	VDRM Repetitive peak off-state voltage		400	V

ABSOLUTE MAXIMUM RATINGS: DIODES

Symbol	Parameter		Value			Linit			
	- arameter		D1	D2	D3	D4	Unit		
IFRM	Repetitive peak forward current (Note 1)	Tl= 110 ℃	1	100	100	1	Α		
I _{FSM}	Non repetitive surge forward current	tp = 20 μs	15	150	150	15	Α		
	Tj initial = Tj = 25°C	tp = 10 ms	2	5	5	2	Α		
VRRM	Repetitive peak off-state voltage	Tj= 125 ℃	25	400	400	25	٧		

Note 1: Test current waveform



ABSOLUTE MAXIMUM RATINGS: FOR ALL DEVICES (ICC01)

Symbol	Parameter	Value	Unit	
T _{stg} T _j	Storage temperature range Operating junction temperature range	- 40 to +150 - 40 to +150	°C	
TI	Maximum lead temperature for soldering during 10s	260	°C	

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
Rth(j-a)	Thermal resistance junction to ambient	90	°C/W

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ELECTRICAL CHARACTERISTICS: THYRISTOR TH

Symbol	Test Conditions			Value	Unit
lgт	V _D =12V (DC) R _L =33Ω	Tj= 25°C	MAX	1	mA
V _{GT}	V _D =12V (DC) R _L =33Ω	Tj= 25°C	MAX	1.5	>
V _{TM}	I _{TM} = 4A tp ≤ 1ms	Tj= 25°C	MAX	1.9	V
IDRM	V _{DRM} rated	Tj= 25°C	MAX	50	μА
		Tj= 125°C	MAX	1	mA

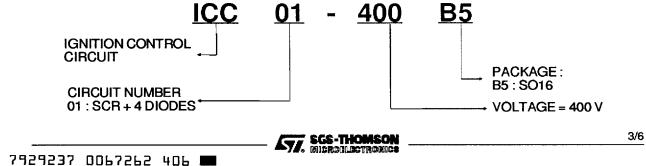
ELECTRICAL CHARACTERISTICS: DIODE D1/D4

Symbol	Test Conditions			Value	Unit
l _R	VR = VRRM	Tj= 25°C	MAX	50	μΑ
		Tj= 120°C	MAX	1	mA
V _F	I _F = 100 mA tp ≤ 1ms	Tj= 25°C	MAX	1.2	٧

ELECTRICAL CHARACTERISTICS: DIODE D2/D3

Symbol	Test Conditions			Value	Unit
IR	Vn = Vnnm	Tj= 25°C	MAX	50	μA
		Tj= 125°C	MAX	1	mA
VF	l _F = 4 A tp ≤ 1ms	Tj= 25°C	MAX	1.9	٧

ORDERING INFORMATION



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Fig.1: Relative variation of gate trigger current versus junction temperature.

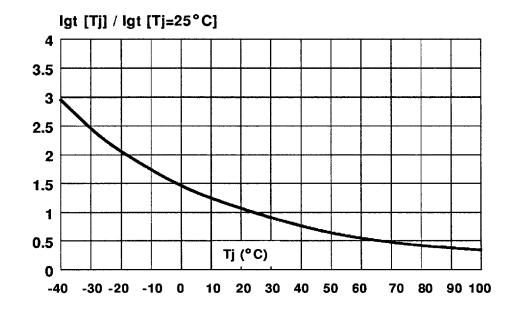
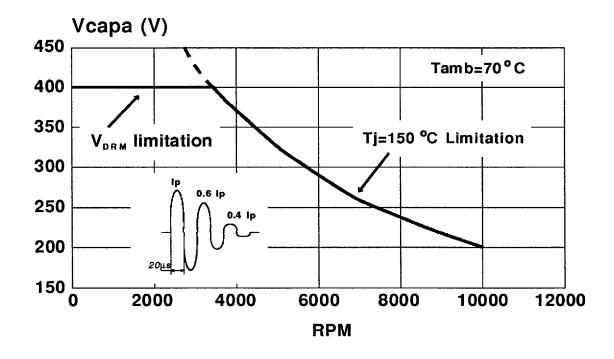


Fig.2: Safety limitation curve of the capacitor voltage variation versus RPM @ tp=20µs.

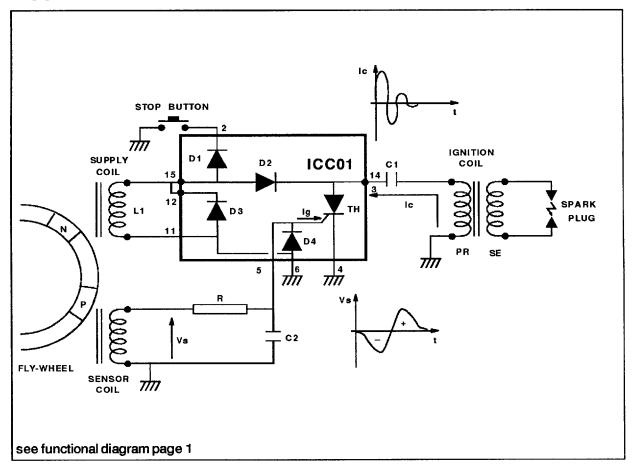


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BASIC APPLICATION



The applications using the capacitive ignition system (CDI) operate in 3 phases.

PHASE 1

Storage of the energy in the capacitor C1

PHASE 2

Discharge of the capacitor C1 and spark generation to the ignition coil.

PHASE 3

Engine stop.

1) ENERGY STORAGE IN C1

The coil L1 generates an alternative voltage. Its positive part charges the capacitor C1 through the diode D2.

The negative waves are clamped by the diode D3.

2) SPARK GENERATION

For each fly-wheel revolution the sensor coil produces a bidirectional pulse Vs and triggers the ignition coil.

The negative sinewave generated is clamped by D4 while the positive sinewave initiates a current la through the thyristor gate (Th)

The firing of the SCR causes an alternating discharge current Ic through the capacitor C1.

The positive parts of this current flow in the loop C1, Th and the primary of the ignition coil PR.

The negative parts flow through C1, PR and both diodes D3 and D2.

3) ENGINE STOP

The engine stop is obtained by short circuiting the supply coil L1 (stop button). The diode D1 avoids the accidental connection of battery voltage.

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R RESISTOR CALCULATION

The purpose of the resistor R is to limit the current lg through the thyristor gate. Its maximum value can be calculated as follow:

R max = (Vs min - Vgt max) / 2 lgt max

POWER LOSSES (For 20µs - see note 1)

The following equations can be used to evaluate power losses:

For TH V_{TO} = 2.65V Rt = 0.110 Ω For D3 V_{FO} = 1.73V Rd = 0.075 Ω

PACKAGE MECHANICAL DATA

SO16 (Plastic)

PROTECTION AGAINST PARASITIC SPIKES

The capacitor C2 in relation with R acts as a filter and avoids the unexpected firing of the thyristor due to parasitic spikes. Good results have been obtained with 10nF capacitance.

		DIMENSIONS						
	REF.	Millimeters			Inches		\$	
		Min.	Тур.	Max.	Min.	Тур.	Max.	
	Α			1.75			0.069	
L G	a1	0.1		0.25	0.004		0.010	
9 3	a2			1.6			0.063	
	b	0.35		0.46	0.014		0.018	
b e3 s la1 lb1	b1	0.19		0.25	0.007		0.010	
←	С		0.5			0.020		
D (1)	c1		45°(typ.)					
	D	9.8		10	0.386		0.394	
16 9	E	5.8		6.2	0.228		0.244	
F (1) (1) Do not include mold	е		1.27			0.050		
flesh or protrusions Mold flash or protrusions shall not exceed 0 15mm	е3		8.89			0.350		
(0 006inches)	F	3.8		4.0	0.150		0.158	
	G	4.6		5.3	0.181		0.209	
	L	0.4		1.27	0.016		0.050	
	М			0.62			0.024	
	S			8°(t	yp.)			

Marking: ICC1-400 Weight: 0.15 g

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